

Zhe Ashley Jian

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8225941/publications.pdf>

Version: 2024-02-01

10
papers

115
citations

1478505

6
h-index

1474206

9
g-index

10
all docs

10
docs citations

10
times ranked

165
citing authors

#	ARTICLE	IF	CITATIONS
1	Temperature-dependent current-voltage characteristics of $\text{In}^2\text{-Ga}_2\text{O}_3$ trench Schottky barrier diodes. Applied Physics Letters, 2020, 116, .	3.3	41
2	Chlorine-based inductive coupled plasma etching of $\text{In}^{\pm}\text{-Ga}_2\text{O}_3$. Semiconductor Science and Technology, 2019, 34, 035006.	2.0	15
3	Deep UV-assisted capacitance-voltage characterization of post-deposition annealed $\text{Al}_2\text{O}_3/\text{In}^2\text{-Ga}_2\text{O}_3$ (001) MOSCAPs. Applied Physics Letters, 2020, 116, .	3.3	14
4	Switching Performance Analysis of 3.5 kV Ga_2O_3 Power FinFETs. IEEE Transactions on Electron Devices, 2021, 68, 672-678.	3.0	12
5	Characterization of MOCVD-grown AlSiO gate dielectric on $\text{In}^2\text{-Ga}_2\text{O}_3$ (001). Applied Physics Letters, 2021, 118, .	3.3	10
6	Investigation and optimization of HfO ₂ gate dielectric on N-polar GaN: Impact of surface treatments, deposition, and annealing conditions. Applied Physics Letters, 2021, 119, .	3.3	9
7	Design of ultra-scaled-channel N-polar GaN HEMTs with high charge density: A systematic study of hole traps and their impact on charge density in the channel. Journal of Applied Physics, 2020, 128, .	2.5	5
8	HfO ₂ as gate insulator on N-polar GaN-AlGaIn heterostructures. Semiconductor Science and Technology, 0, , .	2.0	4
9	Improved operational reliability of MOCVD-grown AlSiO gate dielectric on $\text{In}^2\text{-Ga}_2\text{O}_3$ (001) by post-metallization annealing. Semiconductor Science and Technology, 2021, 36, 09LT03.	2.0	3
10	Demonstration of atmospheric plasma activated direct bonding of N-polar GaN and $\text{In}^2\text{-Ga}_2\text{O}_3$ (001) substrates. Applied Physics Letters, 2022, 120, .	3.3	2